

**IN THE SPECIFICATION:**

**Page 14, first full paragraph, delete and insert the following:**

Q1 The construction of a semiconductor laser device as the second embodiment of the present invention and a process of producing the construction are explained with reference to Fig. 3, which is a cross-sectional view of the semiconductor laser device as the second embodiment.

**IN THE CLAIMS:**

**Cancel claim 1 without prejudice or disclaimer.**

2 (Amended). A semiconductor laser device having an index-guided structure and oscillating in a fundamental mode, comprising:

Q2

- a lower cladding layer;
- a lower optical waveguide layer formed above said lower cladding layer;
- a quantum well layer formed above said lower optical waveguide layer;
- an upper optical waveguide layer formed above said quantum well layer; and
- a current confinement structure formed above said upper optical waveguide layer;

said upper optical waveguide layer has a first thickness smaller than a second thickness of said lower optical waveguide layer;

wherein a sum of said first and second thickness is 0.5 micrometers or greater.